



#19/Amdt C  
6.23.03  
C. Moore

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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :  
AKIRA NISHIYAMA, ET AL. : EXAMINER: MAI, A.  
SERIAL NO: 09/891,129 :  
RCE FILED: HEREWITH : GROUP ART UNIT: 2814  
FOR: SEMICONDUCTOR DEVICE :  
HAVING AN INSULATING FILM  
MADE OF A HIGHLY DIELECTRIC  
THIN FILM AND METHOD OF  
MANUFACTURING THE SAME

RECEIVED  
JUN 11 2003  
TECHNOLOGY CENTER 2800

AMENDMENT FILED CONCURRENTLY WITH  
REQUEST FOR CONTINUED EXAMINATION (RCE)

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to a further examination on the merits, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend claims 1 and 16 to read as follows:<sup>1</sup>

C1  
1. (Twice Amended) A semiconductor device comprising:  
a semiconductor substrate, and  
a circuit element using an insulating film formed on said semiconductor substrate,  
said insulating film containing a silicon compound containing oxygen, and a metal  
compound containing a metal other than silicon and oxygen, said insulating film further